

3-W High-Voltage Switchmode Regulator

DESCRIPTION

The Si9102 high-voltage switchmode regulator is a monolithic BiC/DMOS integrated circuit which contains most of the components necessary to implement a high-efficiency dc-to-dc converter up to 3 watts. It can either be operated from a low-voltage dc supply, or directly from a 10 to 120 V unregulated dc power source.

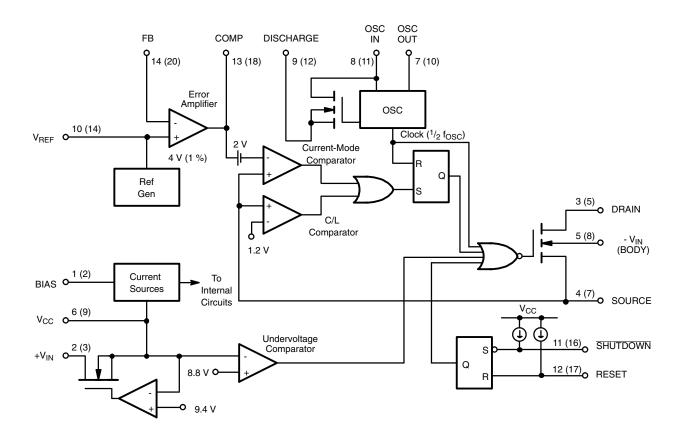
This device may be used with an appropriate transformer to implement most single-ended isolated power converter topologies (i.e., flyback and forward).

The Si9102 is available in both standard and lead (Pb)-free 14-pin plastic DIP and 20-pin PLCC packages which are specified to operate over the industrial temperature range of - 40 °C to 85 °C.

FEATURES

- 10 to 120 V Input Range
- · Current-Mode Control
- On-chip 200 V, 7 Ω MOSFET Switch
- SHUTDOWN and RESET
- High Efficiency Operation (> 80 %)
- Internal Start-Up Circuit
- Internal Oscillator (1 MHz)

FUNCTIONAL BLOCK DIAGRAM



Note: Figures in parenthesis represent pin numbers for 20-pin package.

Si9102

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ABSOLUTE MAXIMUM RATING	is				
Parameter	Limit	Unit			
Voltages Referenced to - V _{IN} (V _{CC} < + V _{IN} +	0.3 V)				
V _{CC}		15			
+V _{IN}		120	V		
V _{DS}		200			
I _D (Peak) (Note: 300 μs pulse, 2 % duty cycle)	2	Α		
I _D (rms)		250	mA		
Logic Inputs (RESET, SHUTDOWN, OSC IN)	- 0.3 V to V _{CC} + 0.3 V	V			
Linear Inputs (FEEDBACK, SOURCE)	- 0.3 to 7				
HV Pre-Regulator Input Current (continuous)		3	mA		
Storage Temperature		- 65 to 125			
Operating Temperature		- 40 to 85	°C		
Junction Temperature (T _J)		150			
Davier Dissipation (Davies and	14-Pin Plastic DIP (J Suffix) ^b	750	mW		
Power Dissipation (Package) ^a	20-Pin PLCC (N Suffix) ^c	1400	mvv		
Thermal Impedance (⊕,IA)	14-Pin Plastic DIP	167	°C/W		
memiai impedance (OJA)	20-Pin PLCC	90	- C/W		

Notes:

- a. Device Mounted with all leads soldered or welded to PC board.
- b. Derate 6 mW/°C above 25 °C.
- c. Derate 11.2 mW/°C above 25 °C.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE					
Parameter	Limit	Unit			
Voltages Referenced to - V _{IN}	·				
V _{CC}	9.5 to 13.5	V			
R _{OSC}	25 kΩ to 1 MΩ				
Linear Inputs	0 to 7	V			
+ V _{IN}	10 to 120	V			
fosc	40 kHz to 1 MHz				
Digital Inputs	0 to V _{CC}				

SPECIFICATIONS ^a							
		Test Conditions Unless Otherwise Specified DISCHARGE = - V _{IN} = 0 V		Limits D Suffix - 40 to 85 °C			
		$V_{CC} = 10 \text{ V}, + V_{IN} = 48 \text{ V}$					
Parameter	Symbol	$R_{BIAS} = 390 \text{ k}\Omega$, $R_{OSC} = 330 \text{ k}\Omega$	Temp ^b	Min ^d	Typ ^c	Max ^d	Unit
Reference							
Output Voltage	V _R	OSC IN = - V_{IN} (OSC Disabled) $R_L = 10 \text{ M}\Omega$	Room Full	3.92 3.86	4.0	4.08 4.14	V
Output Impedance ^e	Z _{OUT}		Room	15	30	45	kΩ
Short Circuit Current	I _{SREF}	$V_{REF} = -V_{IN}$	Room	70	100	130	μΑ
Temperature Stability ^e	T _{REF}		Full		0.5	1.0	mV/°C
Oscillator	<u> </u>						
Maximum Frequency ^e	f _{MAX}	$R_{OSC} = 0$	Room	1	3		MHz
Initial Accuracy	f	$R_{OSC} = 330 \text{ k}\Omega^g$	Room	80	100	120	kHz
Illiai Accuracy	†osc	$R_{OSC} = 150 \text{ k}\Omega^g$	Room	160	200	240	NI IZ
Voltage Stability	∆f/f	$\Delta f/f = f(13.5 \text{ V}) - f(9.5 \text{ V})/f(9.5 \text{ V})$	Room		10	15	%
Temperature Coefficient ^e	T _{OSC}		Full		200	500	ppm/°C





		Test Conditions Unless Otherwise Specified DISCHARGE = - V _{IN} = 0 V		Limits D Suffix - 40 to 85 °C		85 °C	
_		$V_{CC} = 10 \text{ V}, + V_{IN} = 48 \text{ V}$		d		4	l
Parameter	Symbol	$R_{BIAS} = 390 \text{ k}\Omega, R_{OSC} = 330 \text{ k}\Omega$	Temp ^b	Min ^d	Typ ^c	Max ^d	Uni
Error Amplifier		ED Tied to COMP			I	<u> </u>	
Feedback Input Voltage	V _{FB}	FB Tied to COMP OSC IN = - V_{IN} (OSC Disabled)	Room	3.96	4.00	4.04	V
Input BIAS Current	I _{FB}		Room		25	500	nΑ
Open Loop Voltage Gain ^e	A _{VOL}	OSC IN = - V_{IN} , $V_{FB} = 4 V$,	Room	60	80		dE
Unity Gain Bandwidth ^e	BW	OSC IN = - V _{IN} (OSC Disabled)	Room	0.7	1		MH
Dynamic Output Impedance ^e	Z _{OUT}		Room		1000	2000	Ω
Output Current	I _{OUT}	Source (V _{FB} = 3.4 V)	Room		- 2.0	- 1.4	m.
Input OFFSET Voltage	V _{OS}	OSC IN = - V _{IN} (OSC Disabled)	Room		± 15	± 40	m'
Output Current	I _{OUT}	Sink (V _{FB} = 4.5 V)	Room	0.12	0.15		m.
Power Supply Rejection	PSRR	9.5 V ≤ V _{CC} ≤ 13.5 V	Room	50	70		dl
Current Limit	_ I				I	1	
Threshold Voltage	V _{SOURCE}	R_L = 100 Ω from DRAIN to V_{CC} V_{FB} = 0 V	Room	1.0	1.2	1.4	١
Delay to Output ^e	t _d	R_L = 100 Ω from DRAIN to V_{CC} V_{SOURCE} = 1.5 V, See Figure 1	Room		100	200	n
Pre-Regulator/Start-Up					•		
nput Voltage	+ V _{IN}	$I_{IN} = 10 \mu A$	Room			120	١
Input Leakage Current	+ I _{IN}	V _{CC} ≥ 10 V	Room			10	μ
Pre-Regulator Start-Up Current	I _{START}	Pulse Width \leq 300 μ s, $V_{CC} = 7 \text{ V}$	Room	8	15		m
V _{CC} Pre-Regulator Turn-Off Threshold Voltage	V _{REG}	I _{PRE-REGULATOR} = 10 μA	Room	7.8	9.4	9.7	
Undervoltage Lockout	V _{UVLO}	R_L = 100 Ω from DRAIN to V_{CC} See Detailed Description	Room	7.0	8.8	9.2	١
V _{REG} , - V _{UVLO}	V_{DELTA}		Room	0.3	0.6		
Supply							
Supply Current	I _{CC}		Room	0.45	0.6	1.0	m
Bias Current	I _{BIAS}		Room	10	15	20	μ
Logic							
SHUTDOWN Delay ^e	t _{SD}	V _{SOURCE} = - V _{IN} , See Figure 2	Room		50	100	
SHUTDOWN Pulse Width ^e	t _{SW}		Room	50			
RESET Pulse Width ^e	t _{RW}	See Figure 3	Room	50			n
Latching Pulse Width ^e SHUTDOWN and RESET Low	t _{LW}	J	Room	25			
Input Low Voltage	V _{IL}		Room			2.0	\
Input High Voltage	V _{IH}		Room	8.0			`
Input Current Input Voltage High	I _{IH}	V _{IN} = 10 V	Room		1	5	μ
Input Current Input Voltage Low	I _{IL}	V _{IN} = 0 V	Room	- 35	- 25		μ,
MOSFET Switch							
Breakdown Voltage	V _{BR(DSS)}	I _{DRAIN} = 100 μA	Full	200	220		V
Drain-Source On Resistance ^f	r _{DS(on)}	I _{DRAIN} = 100 mA	Room			7	Ω
Drain Off Leakage Current	I _{DSS}	V _{DRAIN} = 100 V	Room		5	10	μ
Drain Capacitance	C _{DS}		Room		35		рF

- a. Refer to PROCESS OPTION FLOWCHART for additional information.

- a. Herer to PHOCESS OF HON FLOWCHART for additional information.
 b. Room = 25 °C, Full = as determined by the operating temperature suffix.
 c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
 d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
 e. Guaranteed by design, not subject to production test.
 f. Temperature coefficient of r_{DS(on)} is 0.75 % per °C, typical.
 g. C_{STRAY} Pin 8 = ≤ 5 pF.

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TIMING WAVEFORMS

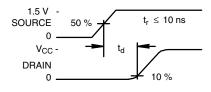


Figure 1.

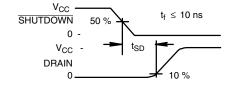


Figure 2.

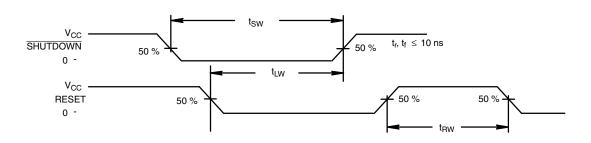


Figure 3.

TYPICAL CHARACTERISTICS

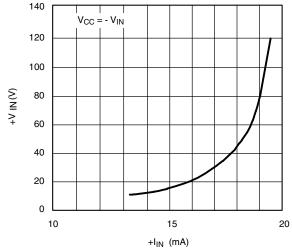


Figure 4. + V_{IN} vs. + I_{IN} at Start-Up

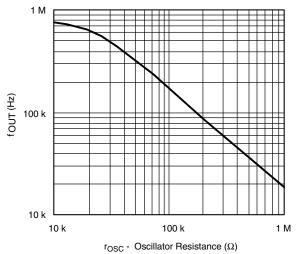


Figure 5. Output Switching Frequency vs. Oscillator Resistance

PIN DESCRIPTION

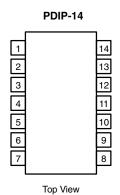
Function



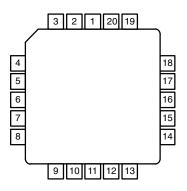
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Pin

PIN CONFIGURATIONS



PLCC-20



Top View

14-Pin DIP 20-Pin PLCC* **BIAS** $+ V_{IN}$ 2 3 DRAIN 3 5 7 SOURCE 4 - V_{IN} 5 8 V_{CC} 6 9 OSC OUT 7 10 OSC IN 8 11 DISCHARGE 9 12 V_{REF} 10 14 SHUTDOWN 11 16 RESET 12 17 COMP 13 18 FΒ 14 20 *Pins 1, 4, 6, 13, 15, and 19 = N/C

ORDERING INFORMATION					
Standard Part Number	Lead (Pb)-free Part Number	Temperature Range	Package		
Si9102DJ02	Si9102DJ02-E3		PDIP-14		
Si9102DN02	Si9102DN02-E3				
Si9102DN02-T1 (With Tape and Reel)	Si9102DN02-T1-E3 (With Tape and Reel)	- 40 to 85 °C	PLCC-20		

DETAIL DESCRIPTION

Pre-Regulator/Start-Up Section

Due to the low quiescent current requirement of the Si9102 control circuitry, bias power can be supplied from the unregulated input power source, from an external regulated low-voltage supply, or from an auxiliary "bootstrap" winding on the output inductor or transformer.

When power is first applied during start-up, + V_{IN} will draw a constant current. The magnitude of this current is determined by a high-voltage depletion MOSFET device which is connected between + V_{IN} and V_{CC} . This start-up circuitry provides initial power to the IC by charging an external bypass capacitance connected to the V_{CC} pin. The constant current is disabled when V_{CC} exceeds 9.4 V. If V_{CC} is not forced to exceed the 9.4 V threshold, then V_{CC} will be regulated to a nominal value of 9.4 V by the pre-regulator circuit.

As the supply voltage rises toward the normal operating conditions, an internal undervoltage (UV) lockout circuit keeps the output MOSFET disabled until $\rm V_{CC}$ exceeds the undervoltage lockout threshold (typically 8.8 V). This guarantees that the control logic will be functioning properly and that sufficient gate drive voltage is available before the MOSFET turns on. The design of the IC is such that the undervoltage lockout threshold will not exceed the pre-regulator turn-off voltage. Power dissipation can be minimized by providing an external power source to $\rm V_{CC}$ such that the constant current source is always disabled.

Note: During start-up or when V_{CC} drops below 9.4 V the start-up circuit is capable of sourcing up to 20 mA. This may lead to a high level of power dissipation in the IC (for a 48 V input, approximately 1 W). Excessive start-up time caused by external loading of the V_{CC} supply can result in device damage. Figure 4 gives the typical pre-regulator current at start-up as a function of input voltage.

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DETAIL DESCRIPTION

BIAS

To properly set the bias for the Si9102, a 390 k Ω resistor should be tied from BIAS to - V_{IN}. This determines the magnitude of bias current in all of the analog sections and the pull-up current for the SHUTDOWN and RESET pins. The current flowing in the bias resistor is nominally 15 μ A.

Reference Section

The reference section of the Si9102 consists of a temperature compensated buried zener and trimmable divider network. The output of the reference section is connected internally to the non-inverting input of the error amplifier. Nominal reference output voltage is 4 V. The trimming procedure that is used on the Si9102 brings the output of the error amplifier (which is configured for unity gain during trimming) to within $\pm\,1\,\%$ of 4 V. This automatically compensates for the input offset voltage in the error amplifier.

The output impedance of the reference section has been purposely made high so that a low impedance external voltage source can be used to override the internal voltage source, if desired, without otherwise altering the performance of the device.

Error Amplifier

Closed-loop regulation is provided by the error amplifier, which is intended for use with "around-the-amplifier" compensation. A MOS differential input stage provides for low input current. The noninverting input to the error amplifier (V_{REF}) is internally connected to the output of the reference supply and should be bypassed with a small capacitor to ground.

Oscillator Section

The oscillator consists of a ring of CMOS inverters, capacitors, and a capacitor discharge switch. Frequency is set by an external resistor between the OSC in and OSC out pins. (See Figure 5 for details of resistor value vs. frequency.) The DISCHARGE pin should be tied to - V_{IN} for normal internal oscillator operation. A frequency divider in the logic section limits switch duty cycle to $\leq 50~\%$ by locking the switching frequency to one half of the oscillator frequency.

Remote synchronization can be accomplished by capacitive coupling of a synchronization pulse into the OSC IN terminal. For a 5 V pulse amplitude and 0.5 μs pulse width, typical values would be 100 pF in series with 3 $k\Omega$ to OSC IN.

SHUTDOWN and RESET

SHUTDOWN and RESET are intended for overriding the output MOSFET switch via external control logic. The two inputs are fed through a latch preceding the output switch. Depending on the logic state of RESET, SHUTDOWN can be either a latched or unlatched input. The output is off whenever SHUTDOWN is low. By simultaneously having SHUTDOWN and RESET low, the latch is set and SHUTDOWN has no effect until RESET goes high. The truth table for these inputs is given in Table 1.

Both pins have internal current source pull-ups and should be left disconnected when not in use. An added feature of the current sources is the ability to connect a capacitor and an open-collector driver to the SHUTDOWN or RESET pins to provide variable shutdown time.

Table 1. Truth Table for the SHUTDOWN and RESET Pins

SHUTDOWN	RESET	Output
Н	Н	Normal Operation
Н	₹_	Normal Operation (No Change)
L	Н	Off (Not Latched)
L	L	Off (Latched)
	L	Off (Latched, No Change)

Output Switch

The output switch is a 7 Ω , 200 V lateral DMOS device. Like discrete MOSFETs, the switch contains an intrinsic bodydrain diode. However, the body contact in the Si9102 is connected internally to - V_{IN} and is independent of the SOURCE.



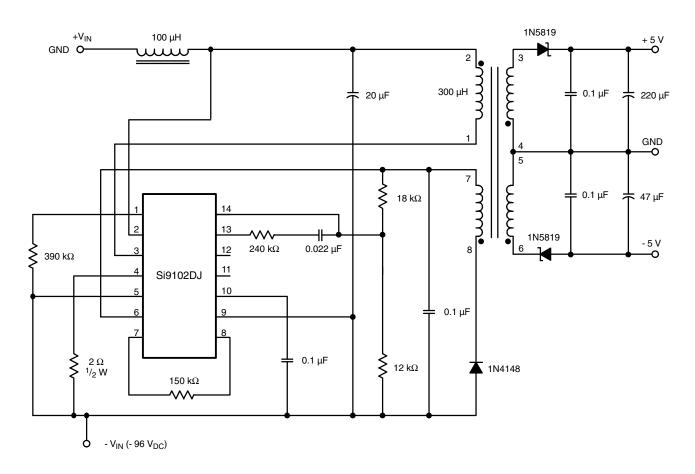
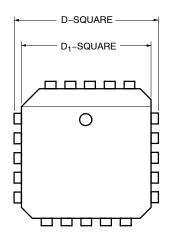


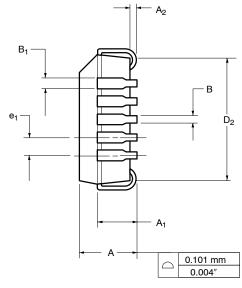
Figure 6. Flyback Converter for Double Battery Telecommunications Power Supplies

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PLCC: 20-LEAD (POWER IC ONLY)

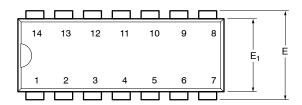


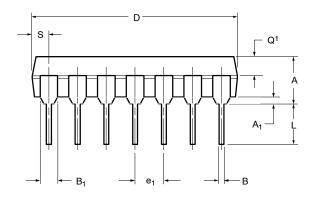


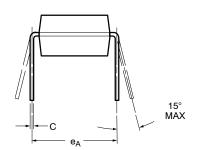
	MILLIMETERS		INC	HES	
Dim	Min	Max	Min	Max	
Α	4.20	4.57	0.165	0.180	
A ₁	2.29	3.04	0.090	0.120	
A ₂	0.51	-	0.020	-	
В	0.331	0.553	0.013	0.021	
B ₁	0.661	0.812	0.026	0.032	
D	9.78	10.03	0.385	0.395	
D ₁	8.890	9.042	0.350	0.356	
D_2	7.37	8.38	0.290	0.330	
e ₁	1.27 BSC 0.050 BSC				
ECN: S-40081—Rev. A, 02-Feb-04 DWG: 5917					



PDIP: 14-LEAD (POWER IC ONLY)







	MILLIMETERS		INC	HES	
Dim	Min	Max	Min	Max	
Α	3.81	5.08	0.150	0.200	
A ₁	0.38	1.27	0.015	0.050	
В	0.38	0.51	0.015	0.020	
B ₁	0.89	1.65	0.035	0.065	
С	0.20	0.30	0.008	0.012	
D	17.27	19.30	0.680	0.760	
E	7.62	8.26	0.300	0.325	
E ₁	5.59	7.11	0.220	0.280	
e ₁	2.29	2.79	0.090	0.110	
e _A	7.37	7.87	0.290	0.310	
L	2.79	3.81	0.110	0.150	
Q ₁	1.27	2.03	0.050	0.080	
S	1.02	2.03	0.040	0.080	
ECN: S-40081—Rev. A, 02-Feb-04 DWG: 5919					

www.vishay.com Document Number: 72814 28-Jan-04



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